

VERSION WITH MARKINGS TO SHOW CHANGES MADE April 4, 2002

In the Specification on page 1:

RELATED INVENTIONS

The invention was made with government support under Grant (Contract) No. NAVY N66001-00-1-8930 awarded by the Defense Advanced Research Projects Agency (DARPA) and monitored by the Space and Naval Warfare Systems Center (SPAWAR), [and] F49620-95-1-0525 awarded by [the Defense Advanced Research Projects Agency (DARPA)] DARPA and monitored by the Air Force Office of Scientific Research (AFOSR), and ECS-0000541 awarded by the National Science Foundation (NSF). The government has certain rights to this invention.

In the Specification on page 16:

In FIGURE 6, we depict the measurement of the thin imaged layer of photoresist taken by a spectrometer before and after the transfer. [The absence of fringes after transfer indicates the film is no longer present on the carrier.] The presence of interference fringes indicates the presence of a thin film. The original spectrum in FIGURE 6(a) indicates a film is present on the original quartz carrier, while FIGURE 6(b) indicates no film is found on the silicon substrate. After transfer, the spectrum in FIGURE 6(c) indicates there is no film left on the quartz carrier, while the spectrum in FIGURE 6(d) indicates the presence of the film on the silicon substrate.